VS-150EBU02



Vishay Semiconductors

Ultrafast Soft Recovery Diode, 150 A FRED Pt®



PRODUCT SUMMARY				
Package	PowerTab [®]			
I _{F(AV)}	150 A			
V _R	200 V			
V _F at I _F	0.79 V			
t _{rr} (typ.)	See recovery table			
T _J max.	175 °C			
Diode variation	Single die			

FEATURES

- Ultrafast recovery time
- 175 °C max. operating junction temperature
- Screw mounting only
- \bullet Designed and qualified according to ${\sf JEDEC}^{\circledast}{\sf -}{\sf JESD}$ 47
- PowerTab[®] package
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION / APPLICATIONS

These diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems.

The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for HF welding, power converters and other applications where switching losses are not significant portion of the total losses.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Cathode to anode voltage	V _R		200	V	
Continuous forward current	I _{F(AV)}	T _C = 116 °C	150		
Single pulse forward current	I _{FSM}	T _C = 25 °C	1600	А	
Maximum repetitive forward current	I _{FRM}	Square wave, 20 kHz	380		
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V _{BR} , V _R	$I_{D} = 100 IIA$		-	-	
Forward voltage	V	I _F = 150 A	-	0.99	1.13	V
Forward voltage V _F	I _F = 150 A, T _J = 175 °C	-	0.79	0.90		
Reverse leakage current		$V_{R} = V_{R}$ rated	-	-	50	μA
Reverse leakage current I _R	$T_J = 150 \ ^{\circ}C, V_R = V_R \text{ rated}$	-	-	2	mA	
Junction capacitance	CT	V _R = 200 V	-	180	-	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body - 3.5 -		nH		

Revision: 09-Jun-15 1 Document Number: 93002 For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		I_F = 1.0 A, dI_F/dt = 200 A/µs, V_R = 30 V		-	-	45	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	34	-	ns
		T _J = 125 °C		-	58	-	
Peak recovery current I _{RRM}		T _J = 25 °C	I _F = 150 A V _R = 160 V dI _F /dt = 200 A/μs	-	4.5	-	А
	IRRM	T _J = 125 °C		-	9.0	-	
Reverse recovery charge Q _{rr}	0	T _J = 25 °C		-	87	-	nC
	Qrr	T _J = 125 °C		-	300	-	10

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal resistance, junction to case	R _{thJC}		-	-	0.35	K/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.2	-	r∨ vv
Weight			-	-	5.02	g
Weight			-	0.18	-	oz.
Mounting torque			1.2 (10)	-	2.4 (20)	N · m (lbf · in)
Marking device		Case style PowerTab [®]	150EBU02			

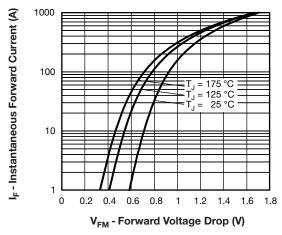


Fig. 1 - Maximum Forward Voltage Drop Characteristics

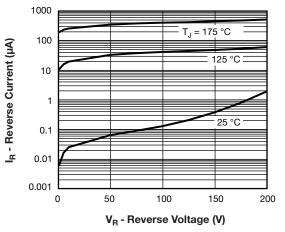


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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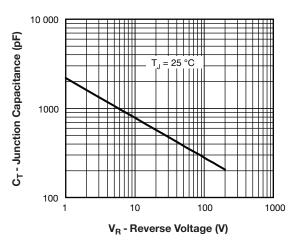


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

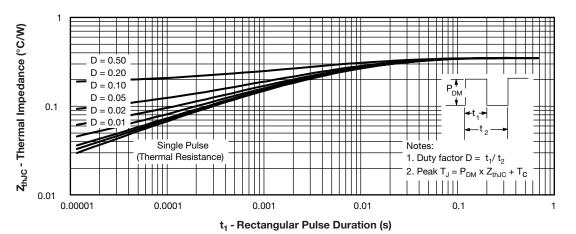
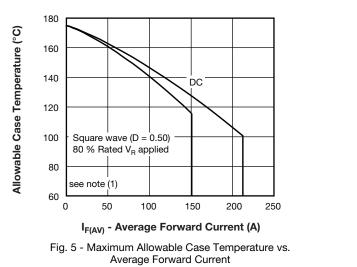
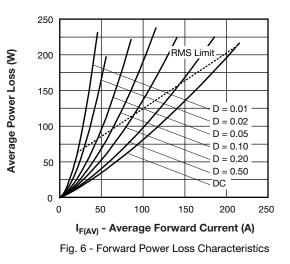


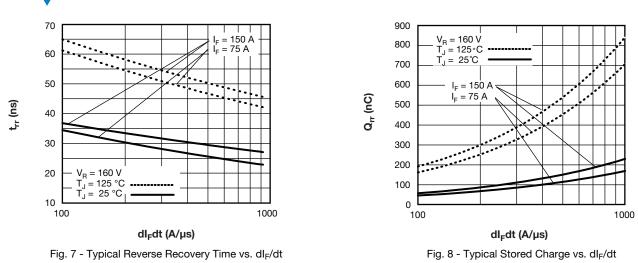
Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics





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Note

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⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; $Pd = Forward power loss = I_{F(AV)} \times V_{FM} at (I_{F(AV)}/D)$ (see fig. 6); $Pd_{REV} = Inverse power loss = V_{R1} \times I_R (1 - D)$; $I_R at V_{R1} = 80 \%$ rated V_R

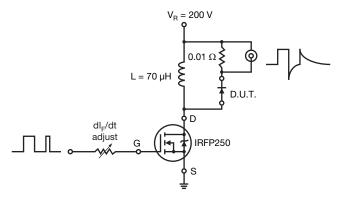


Fig. 9 - Reverse Recovery Parameter Test Circuit

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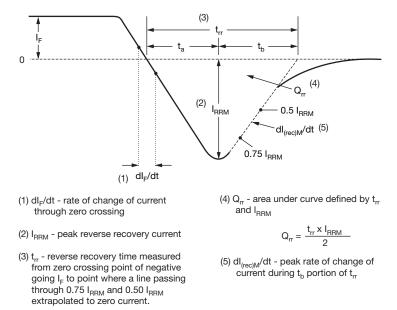
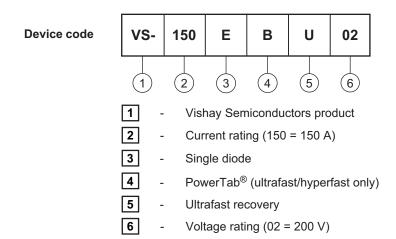


Fig. 10 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

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LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95240			
Part marking information	www.vishay.com/doc?95370			
Application note	www.vishay.com/doc?95179			

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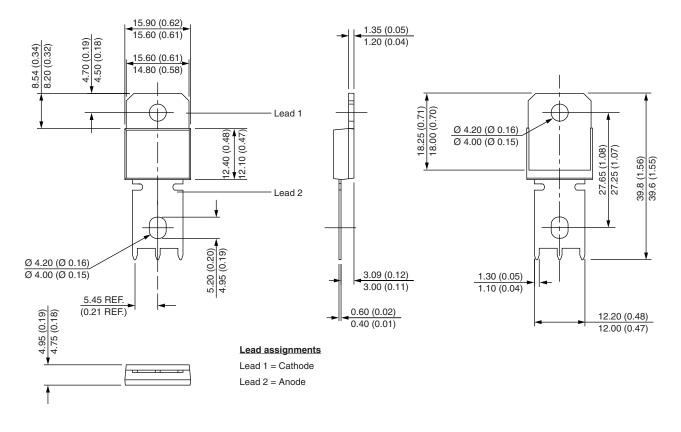
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PowerTab[®]

DIMENSIONS in millimeters (inches)





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